

DMEM and HD cold amp

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For the HD cold amp + DMEM + membrane electronics designers

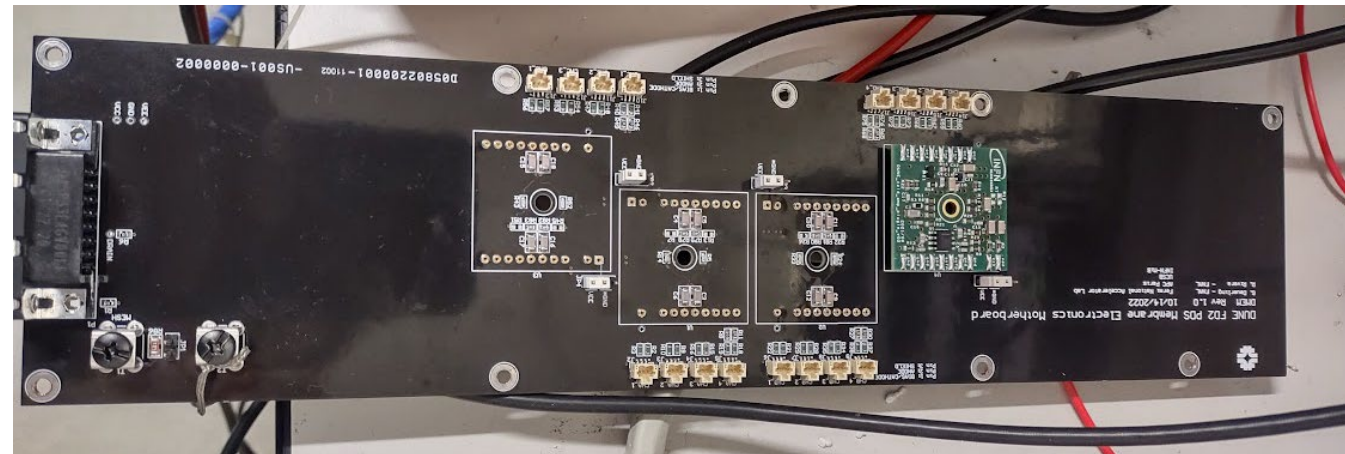
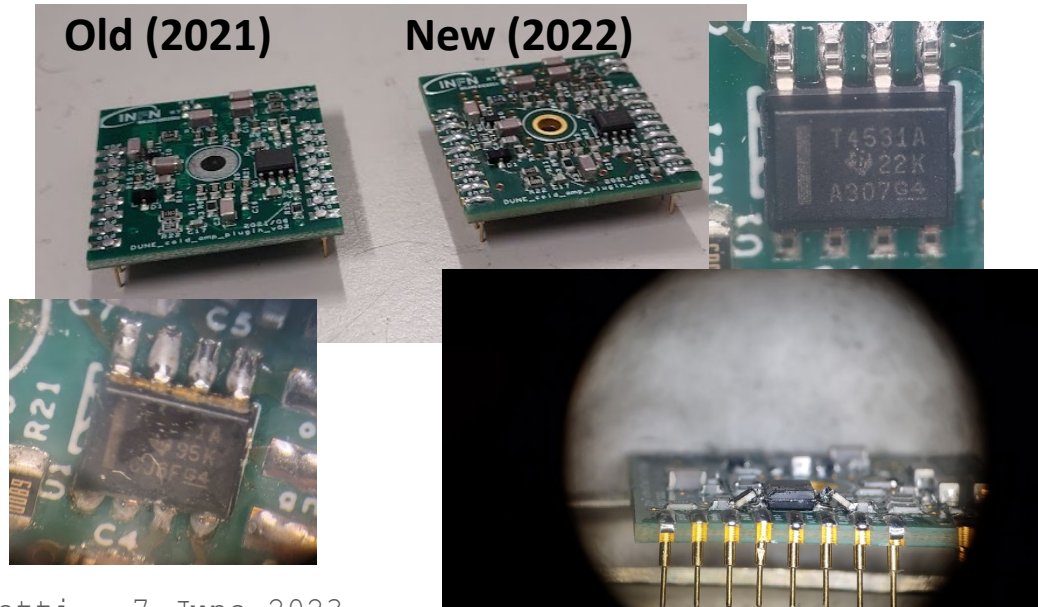
DMEM + HD cold amp

DMEM 1.0 4-channel motherboard designed at FNAL [EDMS 2795424](#)

- 10 produced in 2022
- **3@CERN** (2 in module-0 + 1 in cold box), **4@MiB**, **1@CIEMAT**, **1@Naples(soon)**
- Changes w.r.t. EDMS schematic: $R_f=1.2k$ instead of $2k$ (2 resistors per channel)
- Change will be propagated to all boards (except M1 M2 in module 0)

HD-style amplifiers: same as horizontal drift [EDMS 2805804](#)

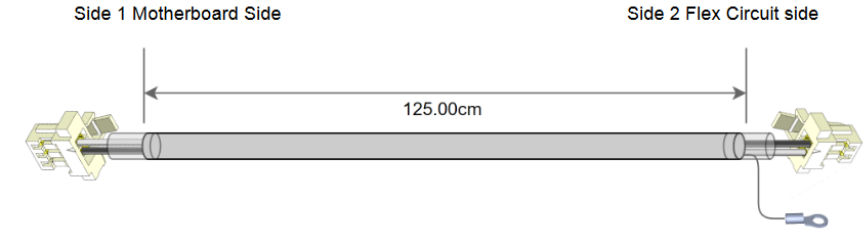
- **8(new)@MiB** (of which 4 in use), **≈ 15 (old)@CIEMAT**, a **few(?)@CERN** (not all in use)
- 50 ohm resistors must be added in series with the THS4531 outputs to prevent instabilities with large (>390 ohm) feedback resistors; likely not necessary with old amplifiers (old batch of THS4531)



Cables

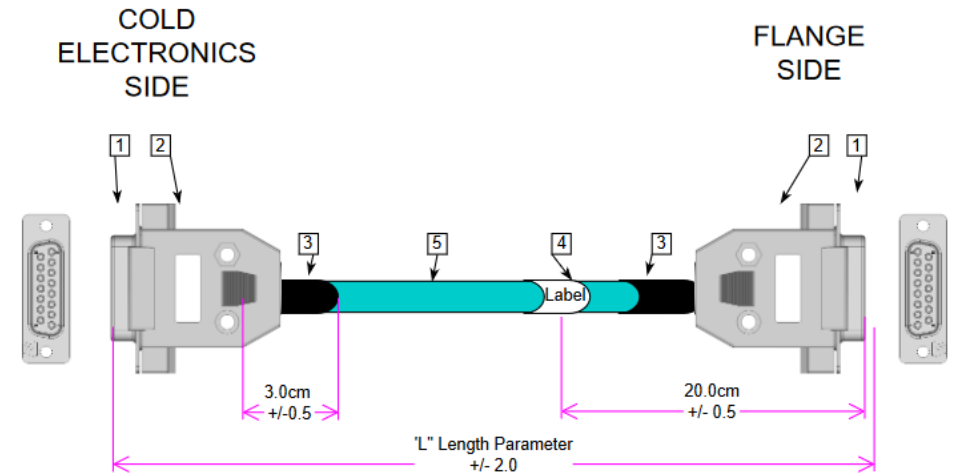
Between flex and DMEM: [EDMS 2815448](#)

- White «coaxial» cables (actually 2 conductors + shielding), about 1m long
- Made/ordered by FNAL



Between DMEM and warm (through flange): [EDMS 2815464](#)

- Blue superior essex cable (same as HD)
- DSUB15 connectors at both ends (differs from HD)
- Cold side (DMEM to flange): female/female
- Warm side (flange to DAPHNE): female/male

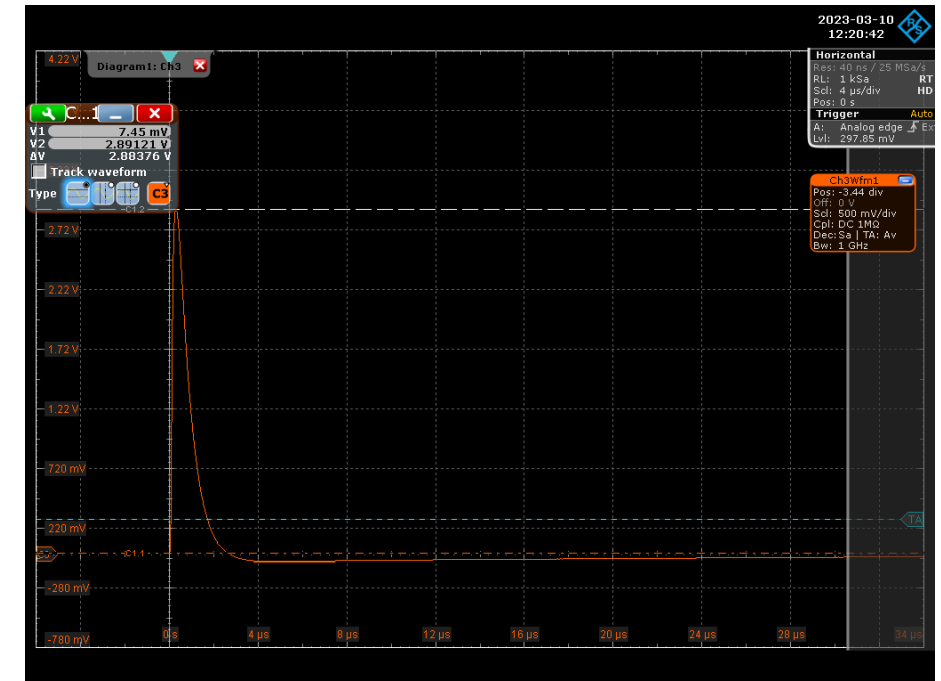
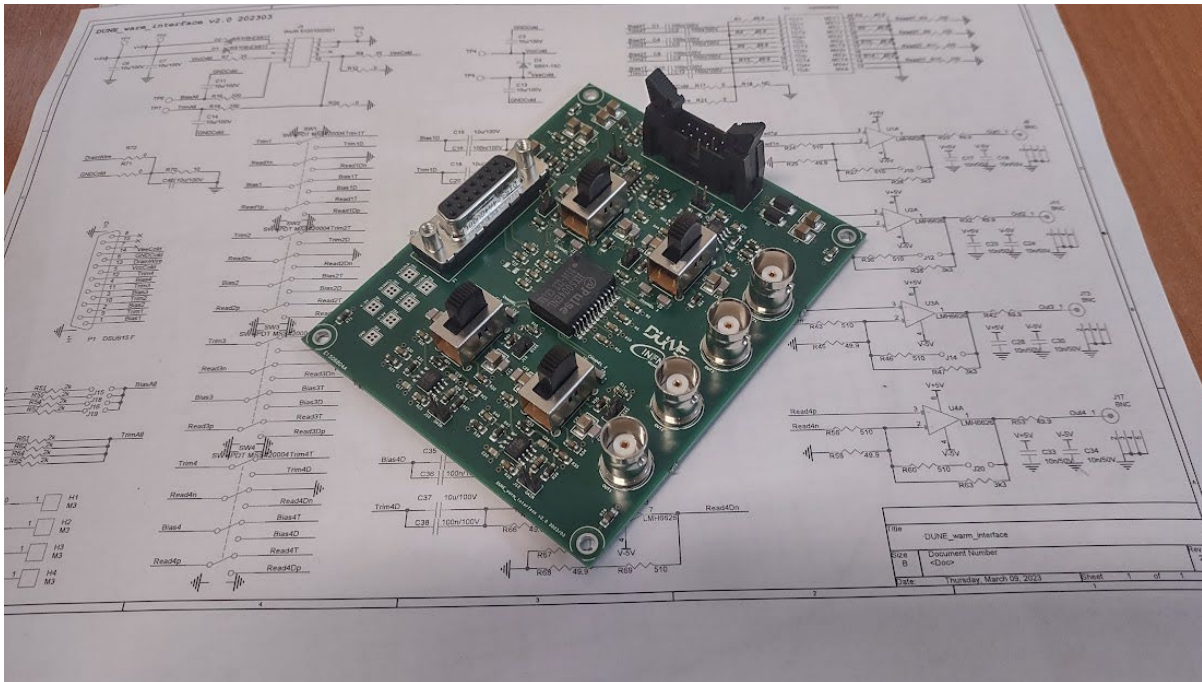


NIOBE-VD flange: [EDMS 2802472](#)

- Male DSUB15 connectors on both sides
- Designed by Jon Ameel (UMich), in use at CERN

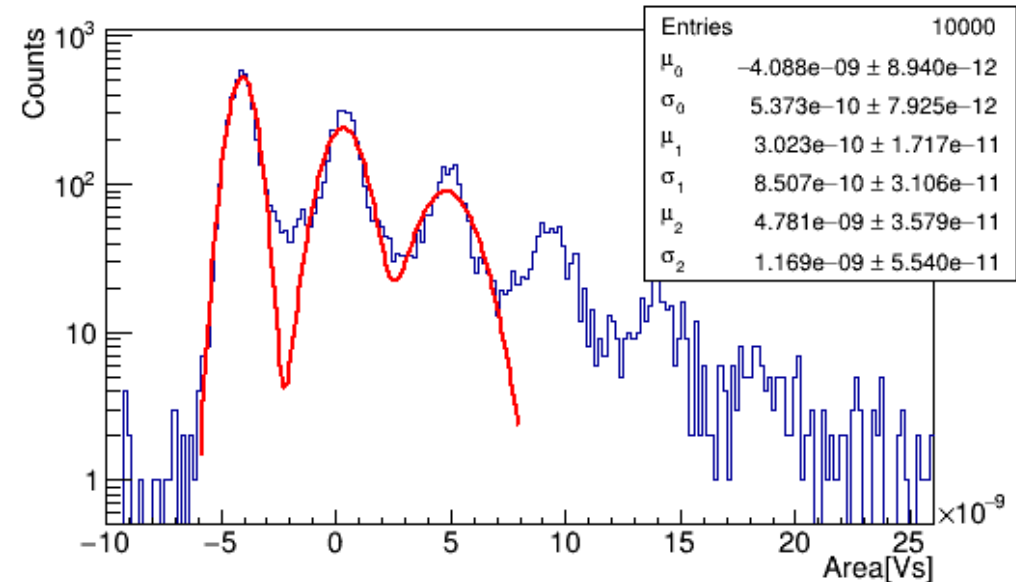
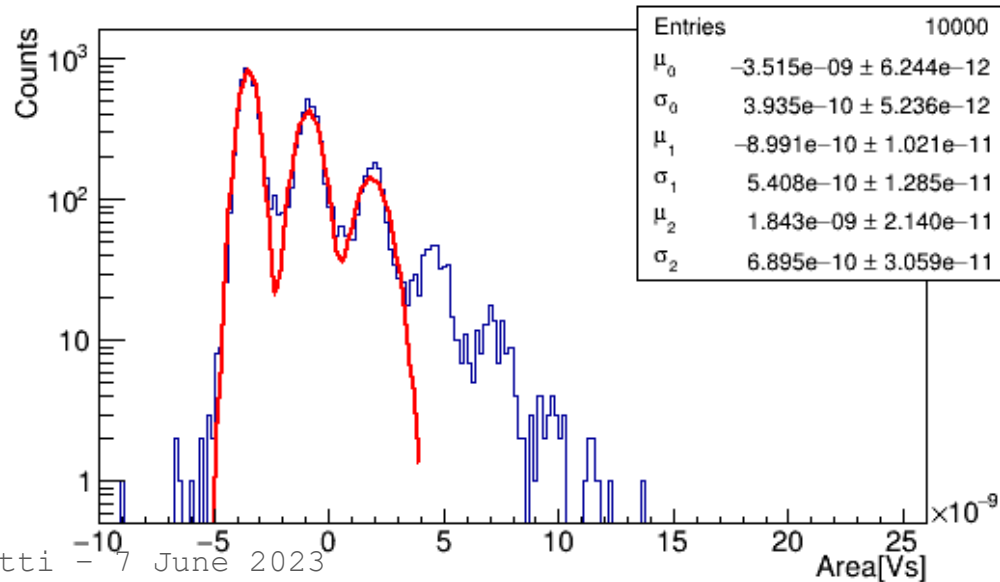
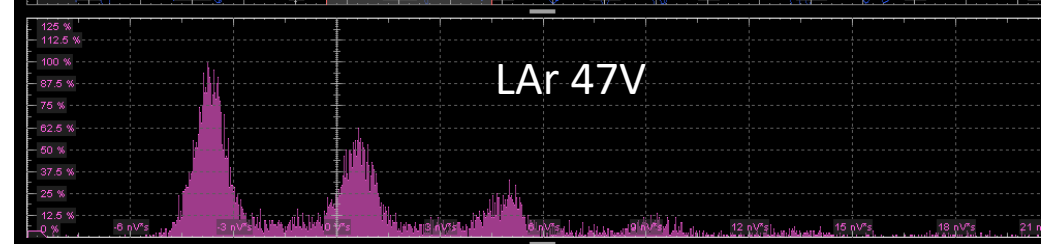
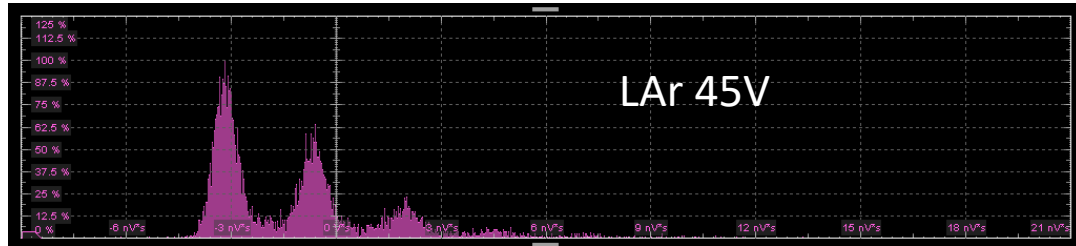
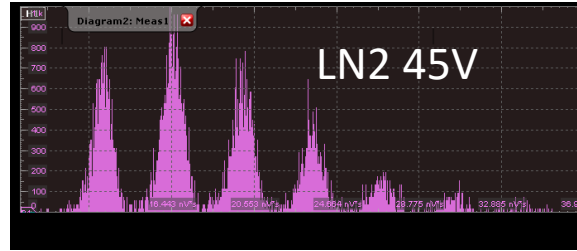
Warm second stage v2

- Interface between DMEM and oscilloscope
- Not needed if DAPHNE is used
- 10 populated boards received last Monday, to be tested
- Design updated from first version
- Two options, selectable with a switch on each channel:
 - Transformer as DAPHNE v3 (undershoot $\approx 8\%$)
 - Transformer bypassed, AC coupled w large caps (undershoot $\approx 3\%$)
(smaller undershoot amplitude means that the tail lasts for longer. In any case the integral of the entire signal has to be zero)



Measured S/N

- In the lab @MiB:
S/N \approx 8 with HPK SiPMs at 45V in LN2 (+3Vov)
- At the march cold box:
S/N \approx 6.7 with HPK SiPMs at 45V in LAr (+2.5Vov)
S/N \approx 8.2 with HPK SiPMs at 47V in LAr (+4.5Vov)



Plans for the near future

- The last configuration tested in the March cold box is still the one to use in future tests (Same as installed in Module-0 M3+M4)
- Tests with ARAPUCA+DMEM are planned to happen soon in Madrid and Naples, which will also validate the electronics further
- Production of additional boards should not be needed before Module-1
- Long term reliability has already been covered for FD1 and passed the FD1 FDR [EDMS 2847126](#)
- Only difference is the presence of 47uF X7R capacitors on the DMEM, not used in FD1, but used in the DCEM